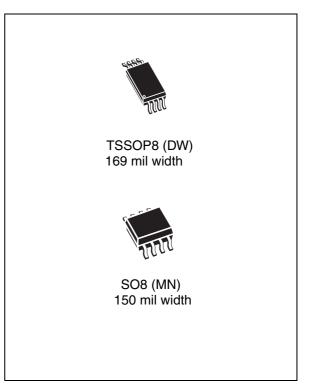


### M24256-125

### Automotive 256-Kbit serial I2C bus EEPROM

#### **Features**

- Compatible with all I<sup>2</sup>C bus modes:
  - 400 kHz Fast mode
  - 100 kHz Standard mode
- Memory array:
  - 256 Kbit (32 Kbytes) of EEPROM
  - Page size: 64 bytes
- Write
  - Byte Write within 5 ms
  - Page Write within 5 ms
- Single supply voltage: 2.5 V to 5.5 V
- Operating temperature range: from -40 °C up to +125 °C
- Random and sequential Read modes
- Write protect of the whole memory array
- Enhanced ESD/Latch-Up protection
- More than 1 million Write cycles
- More than 40-year data retention
- Packages
  - RoHS compliant and halogen-free (ECOPACK<sup>®</sup>)



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Description M24256-125

### 1 Description

The M24256 is a 256-Kbit  $I^2$ C-compatible EEPROM (Electrically Erasable PROgrammable Memory) organized as 32 K  $\times$  8 bits.

This I $^2$ C EEPROM can operate with a supply voltage from 2.5 V up to 5.5 V over an ambient temperature range of -40  $^{\circ}$ C / 125  $^{\circ}$ C.

The device is compliant with the Automotive standard AEC-Q100 grade 1.

Figure 1. Logic diagram

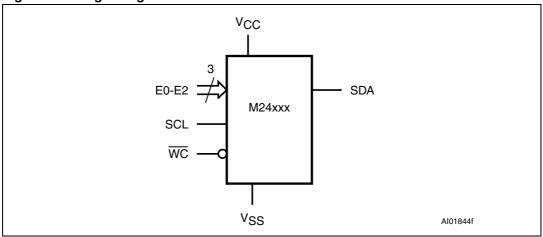
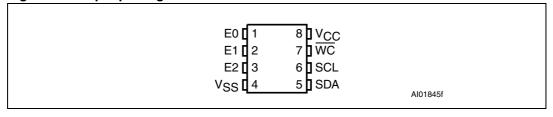


Table 1. Signal names

Signal name	Function	Direction
E2, E1, E0	Chip Enable	Input
SDA	Serial Data	I/O
SCL	Serial Clock	Input
WC	Write Control	Input
V <sub>CC</sub>	Supply voltage	
V <sub>SS</sub>	Ground	

Figure 2. 8-pin package connections



1. See Section 9: Package mechanical data for package dimensions, and how to identify pin 1.



M24256-125 Signal description

### 2 Signal description

### 2.1 Serial Clock (SCL)

This input signal is used to strobe all data in and out of the device. In applications where this signal is used by slave devices to synchronize the bus to a slower clock, the bus master must have an open drain output, and a pull-up resistor must be connected from Serial Clock (SCL) to  $V_{CC}$ . (*Figure 11* indicates how to calculate the value of the pull-up resistor). In most applications, though, this method of synchronization is not employed, and so the pull-up resistor is not necessary, provided that the bus master has a push-pull (rather than open drain) output.

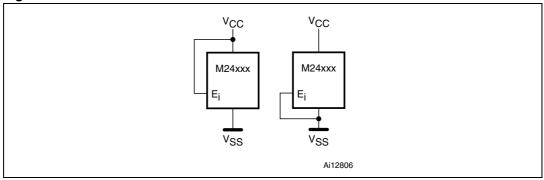
### 2.2 Serial Data (SDA)

This bidirectional signal is used to transfer data in or out of the device. It is an open drain output that may be wire-OR'ed with other open drain or open collector signals on the bus. A pull up resistor must be connected from Serial Data (SDA) to V<sub>CC</sub>. (*Figure 11* indicates how to calculate the value of the pull-up resistor).

### 2.3 Chip Enable (E2, E1, E0)

(E2,E1,E0) input signals are used to set the value that is to be looked for on the three least significant bits (b3, b2, b1) of the 7-bit device select code (see *Table 2*). These inputs must be tied to  $V_{CC}$  or  $V_{SS}$ , as shown in *Figure 3*. When not connected (left floating), these inputs are read as low (0).

Figure 3. Device select code



## 2.4 Write Control (WC)

This input signal is useful for protecting the entire contents of the memory from inadvertent write operations. Write operations are disabled to the entire memory array when Write Control ( $\overline{WC}$ ) is driven high. Write operations are enabled when Write Control ( $\overline{WC}$ ) is either driven low or left floating.

When Write Control (WC) is driven high, device select and address bytes are acknowledged, Data bytes are not acknowledged.

Signal description M24256-125

### $V_{SS}$ (ground)

V<sub>SS</sub> is the reference for the V<sub>CC</sub> supply voltage.

### 2.6 Supply voltage (V<sub>CC</sub>)

#### 2.6.1 Operating supply voltage V<sub>CC</sub>

Prior to selecting the memory and issuing instructions to it, a valid and stable  $V_{CC}$  voltage within the specified [ $V_{CC}$ (min),  $V_{CC}$ (max)] range must be applied (see Operating conditions in *Section 8: DC and AC parameters*). In order to secure a stable DC supply voltage, it is recommended to decouple the  $V_{CC}$  line with a suitable capacitor (usually of the order of 10 nF to 100 nF) close to the  $V_{CC}/V_{SS}$  package pins.

This voltage must remain stable and valid until the end of the transmission of the instruction and, for a write instruction, until the completion of the internal write cycle  $(t_W)$ .

#### 2.6.2 Power-up conditions

The  $V_{CC}$  voltage has to rise continuously from 0 V up to the minimum  $V_{CC}$  operating voltage (see Operating conditions in *Section 8: DC and AC parameters*) and the rise time must not vary faster than 1 V/ $\mu$ s.

#### 2.6.3 Device reset

In order to prevent inadvertent write operations during power-up, a power-on-reset (POR) circuit is included.

At power-up, the device does not respond to any instruction until  $V_{CC}$  has reached the internal reset threshold voltage. This threshold is lower than the minimum  $V_{CC}$  operating voltage (see Operating conditions in *Section 8: DC and AC parameters*). When  $V_{CC}$  passes over the POR threshold, the device is reset and enters the Standby Power mode; however, the device must not be accessed until  $V_{CC}$  reaches a valid and stable DC voltage within the specified  $[V_{CC}(min), V_{CC}(max)]$  range (see Operating conditions in *Section 8: DC and AC parameters*).

In a similar way, during power-down (continuous decrease in  $V_{CC}$ ), the device must not be accessed when  $V_{CC}$  drops below  $V_{CC}$ (min). When  $V_{CC}$  drops below the power-on-reset threshold voltage, the device stops responding to any instruction sent to it.

#### 2.6.4 Power-down conditions

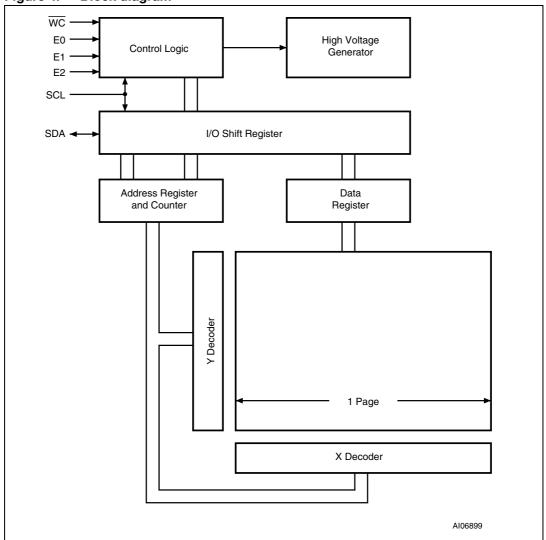
During power-down (continuous decrease in  $V_{CC}$ ), the device must be in the Standby Power mode (mode reached after decoding a Stop condition, assuming that is there is no internal write cycle in progress).

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# 3 Memory organization

The memory is organized as shown in *Figure 4*.

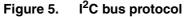
Figure 4. Block diagram

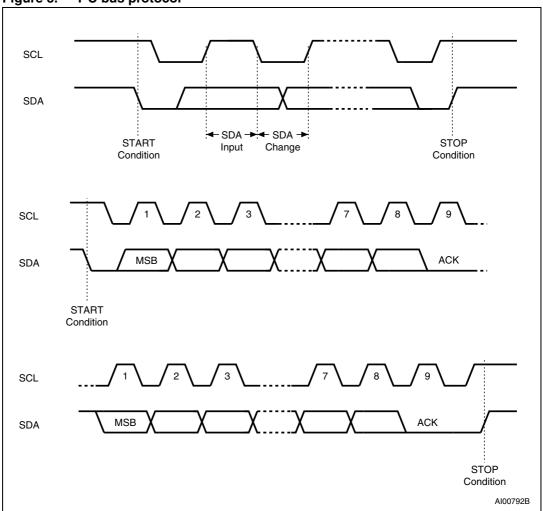


Device operation M24256-125

### 4 Device operation

The device supports the  $I^2C$  protocol. This is summarized in *Figure 5*. Any device that sends data on to the bus is defined to be a transmitter, and any device that reads the data to be a receiver. The device that controls the data transfer is known as the bus master, and the other as the slave device. A data transfer can only be initiated by the bus master, which will also provide the serial clock for synchronization. The device is always a slave in all communications.





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M24256-125 Device operation

#### 4.1 Start condition

Start is identified by a falling edge of Serial Data (SDA) while Serial Clock (SCL) is stable in the high state. A Start condition must precede any data transfer instruction. The device continuously monitors (except during a Write cycle) Serial Data (SDA) and Serial Clock (SCL) for a Start condition.

#### 4.2 Stop condition

Stop is identified by a rising edge of Serial Data (SDA) while Serial Clock (SCL) is stable and driven high. A Stop condition terminates communication between the device and the bus master. A Read instruction that is followed by NoAck can be followed by a Stop condition to force the device into the Standby mode.

A Stop condition at the end of a Write instruction triggers the internal Write cycle.

### 4.3 Acknowledge bit (ACK)

The acknowledge bit is used to indicate a successful byte transfer. The bus transmitter, whether it be bus master or slave device, releases Serial Data (SDA) after sending eight bits of data. During the 9<sup>th</sup> clock pulse period, the receiver pulls Serial Data (SDA) low to acknowledge the receipt of the eight data bits.

#### 4.4 Data input

During data input, the device samples Serial Data (SDA) on the rising edge of Serial Clock (SCL). For correct device operation, Serial Data (SDA) must be stable during the rising edge of Serial Clock (SCL), and the Serial Data (SDA) signal must change *only* when Serial Clock (SCL) is driven low.

### 4.5 Memory addressing

To start communication between the bus master and the slave device, the bus master must initiate a Start condition. Following this, the bus master sends the device select code, shown in *Table 2* (on Serial Data (SDA), most significant bit first).

Table 2. Device select code

	Device type	identifier <sup>(1)</sup>		Chip	R₩		
b7	b6	b5	b4	b3	b3 b2 b1		
1	0	1	0	E2	E1	E0	R₩

<sup>1.</sup> The most significant bit, b7, is sent first.

The device select code consists of a 4-bit device type identifier 1010b, and a 3-bit Chip Enable address (E2, E1, E0). A device select code handling a value other than 1010b is not acknowledged by the device.



<sup>2.</sup> E0, E1 and E2 are compared against the respective external pins on the memory device.

Device operation M24256-125

Up to eight memory devices can be connected on a single  $I^2C$  bus. Each one is given a unique 3-bit code on the Chip Enable (E2, E1, E0) inputs. When the device select code is received, the device only responds if the Chip Enable Address is the same as the value on the Chip Enable (E2, E1, E0) inputs.

The  $8^{th}$  bit is the Read/ $\overline{Write}$  bit (RW). This bit is set to 1 for Read and 0 for Write operations.

If a match occurs on the device select code, the corresponding device gives an acknowledgment on Serial Data (SDA) during the 9<sup>th</sup> bit time. If the device does not match the device select code, it deselects itself from the bus, and goes into Standby mode.

Table 3. Operating modes

Mode	RW bit	<u>₩</u> C <sup>(1)</sup>	Bytes	Initial sequence
Current Address Read	1	х	1	Start, device select, RW = 1
Random Address	0	Х	4	Start, device select, $R\overline{W} = 0$ , Address
Read	1	Х	1	reStart, device select, $R\overline{W} = 1$
Sequential Read 1 X ≥ 1		≥ 1	Similar to Current or Random Address Read	
Byte Write	0	V <sub>IL</sub>	1	Start, device select, $R\overline{W} = 0$
Page Write	0	V <sub>IL</sub>	≤ 64	Start, device select, $R\overline{W} = 0$

<sup>1.</sup>  $X = V_{IH}$  or  $V_{IL}$ .

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M24256-125 Instructions

#### 5 Instructions

#### 5.1 Write operations

Following a Start condition the bus master sends a device select code with the  $R/\overline{W}$  bit  $(R\overline{W})$  reset to 0. The device acknowledges this, as shown in *Figure 6*, and waits for two address bytes. The device responds to each address byte with an acknowledge bit, and then waits for the data byte.

Each byte location is defined by several address bits inside two address bytes. If the address bits are less than 16, the most significant bits (A15 and lower) are Don't Care. The most significant address byte (*Table 4*) is sent first, followed by the least significant address byte (*Table 5*).

When the bus master generates a Stop condition immediately after a data byte Ack bit (in the "10<sup>th</sup> bit" time slot), either at the end of a Byte Write or a Page Write, the internal Write cycle t<sub>W</sub> is triggered. A Stop condition at any other time slot does not trigger the internal Write cycle.

After the Stop condition and the successful completion of an internal Write cycle  $(t_W)$ , the device internal address counter is automatically incremented to point to the next byte after the last modified byte.

During the internal Write cycle, Serial Data (SDA) is disabled internally, and the device does not respond to any requests.

If the Write Control input (WC) is driven High, the Write instruction is not executed and the accompanying data bytes are *not* acknowledged, as shown in *Figure 7*.

Table 4. Most significant address byte

A15 A14 A13 A12 A11 A10 A9	A8
----------------------------	----

Table 5.	Least	significant	address	bvte

A7	A6	A5	A4	А3	A2	A1	A0

Instructions M24256-125

#### 5.1.1 Byte Write

After the device select code and the address bytes, the bus master sends one data byte. If the addressed location is Write-protected, by Write Control ( $\overline{WC}$ ) being driven high, the device replies with NoAck, and the location is not modified. If, instead, the addressed location is not Write-protected, the device replies with Ack. The bus master terminates the transfer by generating a Stop condition, as shown in *Figure 6*.

 $\overline{\mathsf{WC}}$ ACK **ACK ACK** ACK Byte Write Dev sel Byte addr Byte addr Start R/W  $\overline{\mathsf{WC}}$ ACK ACK ACK ACK Page Write Dev sel Byte addr Byte addr Data in 1 Data in 2 R/W WC (cont'd) ACK ACK Data in N Page Write (cont'd) AI01106d

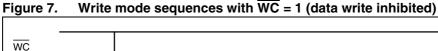
Figure 6. Write mode sequences with  $\overline{WC} = 0$  (data write enabled)

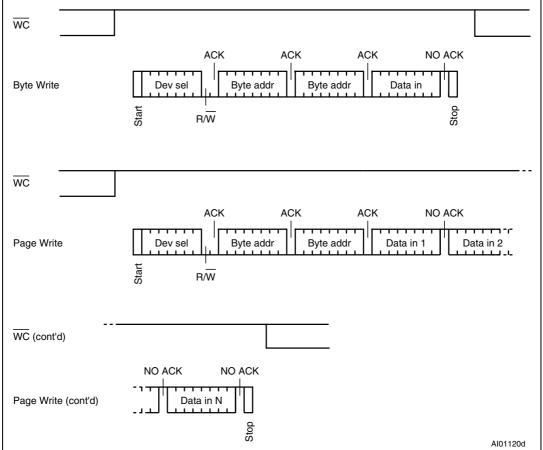
M24256-125 Instructions

#### 5.1.2 **Page Write**

The Page Write mode allows up to 64 bytes to be written in a single Write cycle, provided that they are all located in the same page in the memory: that is, the most significant memory address bits, A14/A6, are the same. If more bytes are sent than will fit up to the end of the page, a condition known as "roll-over" occurs. In case of roll-over, the first bytes of the page are overwritten.

The bus master sends from 1 to 64 bytes of data, each of which is acknowledged by the device if Write Control (WC) is low. If Write Control (WC) is high, the contents of the addressed memory location are not modified, and each data byte is followed by a NoAck, as shown in Figure 7. After each byte is transferred, the internal byte address counter is incremented. The transfer is terminated by the bus master generating a Stop condition.





Instructions M24256-125

#### 5.1.3 ECC (Error Correction Code) and Write cycling

The device offers an ECC (error correction code) logic which compares each 4-byte group with 6 EEPROM bits of ECC. As a result, if a single bit out of 4 bytes of data happens to be erroneous during a read operation, the ECC detects it and replaces it by the correct value. The read reliability is therefore improved by the use of this feature.

Note however that even if a single byte has to be written, 4 bytes are internally modified (plus the ECC bits), that is, the addressed byte is cycled together with the three other bytes making up the group<sup>(a)</sup>. It is therefore recommended to write by groups of 4 bytes in order to benefit from the larger amount of write cycles.

The maximum number of write cycles is qualified at 1 million (1 000 000) write cycles, using a cycling routine that writes to the device by multiples of 4-byte groups.

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a. The group of 4 bytes is located at addresses [4\*N, 4\*N+1, 4\*N+2, 4\*N+3], where N is an integer.

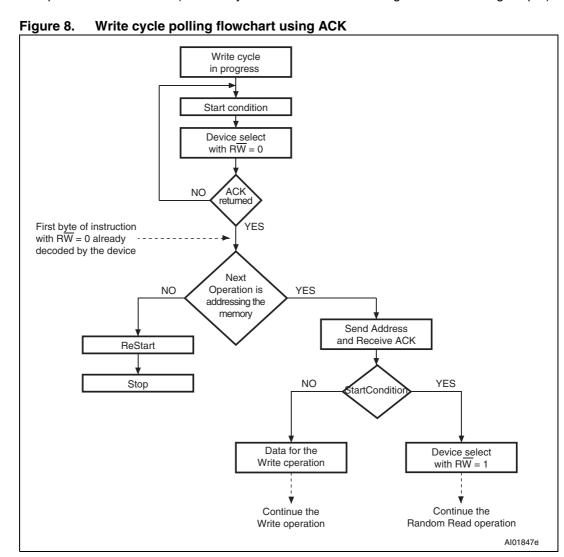
M24256-125 Instructions

#### 5.1.4 Minimizing Write delays by polling on ACK

During the internal Write cycle, the device disconnects itself from the bus, and writes a copy of the data from its internal latches to the memory cells. The maximum Write time  $(t_w)$  is shown in AC characteristics tables in *Section 8: DC and AC parameters*, but the typical time is shorter. To make use of this, a polling sequence can be used by the bus master.

The sequence, as shown in Figure 8, is:

- Initial condition: a Write cycle is in progress.
- Step 1: the bus master issues a Start condition followed by a device select code (the first byte of the new instruction).
- Step 2: if the device is busy with the internal Write cycle, no Ack will be returned and
  the bus master goes back to Step 1. If the device has terminated the internal Write
  cycle, it responds with an Ack, indicating that the device is ready to receive the second
  part of the instruction (the first byte of this instruction having been sent during Step 1).



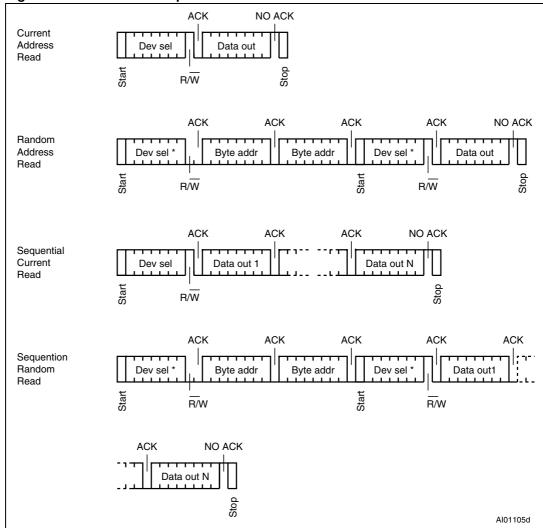
Instructions M24256-125

### 5.2 Read operations

Read operations are performed independently of the state of the Write Control (WC) signal.

After the successful completion of a Read operation, the device's internal address counter is incremented by one, to point to the next byte address.

Figure 9. Read mode sequences



#### 5.2.1 Random Address Read

A dummy Write is first performed to load the address into this address counter (as shown in *Figure 9*) but *without* sending a Stop condition. Then, the bus master sends another Start condition, and repeats the device select code, with the  $R\overline{W}$  bit set to 1. The device acknowledges this, and outputs the contents of the addressed byte. The bus master must *not* acknowledge the byte, and terminates the transfer with a Stop condition.

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M24256-125 Initial delivery state

#### 5.2.2 Current Address Read

For the Current Address Read operation, following a Start condition, the bus master only sends a device select code with the R/W bit set to 1. The device acknowledges this, and outputs the byte addressed by the internal address counter. The counter is then incremented. The bus master terminates the transfer with a Stop condition, as shown in *Figure 9, without* acknowledging the byte.

#### 5.2.3 Sequential Read

This operation can be used after a Current Address Read or a Random Address Read. The bus master *does* acknowledge the data byte output, and sends additional clock pulses so that the device continues to output the next byte in sequence. To terminate the stream of bytes, the bus master must *not* acknowledge the last byte, and *must* generate a Stop condition, as shown in *Figure 9*.

The output data comes from consecutive addresses, with the internal address counter automatically incremented after each byte output. After the last memory address, the address counter 'rolls-over', and the device continues to output data from memory address 00h.

#### 5.2.4 Acknowledge in Read mode

For all Read instructions, the device waits, after each byte read, for an acknowledgment during the 9<sup>th</sup> bit time. If the bus master does not drive Serial Data (SDA) low during this time, the device terminates the data transfer and switches to its Standby mode.

### 6 Initial delivery state

The device is delivered with all the memory array bits set to 1 (each byte contains FFh).

Maximum rating M24256-125

### 7 Maximum rating

Stressing the device outside the ratings listed in *Table 6* may cause permanent damage to the device. These are stress ratings only, and operation of the device at these, or any other conditions outside those indicated in the operating sections of this specification, is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 6. Absolute maximum ratings

Symbol	Parameter	Min.	Max.	Unit
	Ambient operating temperature	-40	130	°C
T <sub>STG</sub>	Storage temperature	-65	150	°C
T <sub>LEAD</sub>	Lead temperature during soldering	see note <sup>(1)</sup>		°C
V <sub>IO</sub>	Input or output range	-0.50	6.5	V
I <sub>OL</sub>	DC output current (SDA = 0)	-	5	mA
V <sub>CC</sub>	Supply voltage	-0.50	6.5	V
V <sub>ESD</sub>	Electrostatic pulse (Human Body model) <sup>(2)</sup>	-	3000	V

Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK® 7191395 specification, and the European directive on Restrictions on Hazardous Substances (RoHS) 2002/95/EU.

<sup>2.</sup> Positive and negative pulses applied on pin pairs, according to AEC-Q100-002 (compliant with JEDEC Std JESD22-A114, C1=100 pF, R1=1500  $\Omega$ , R2=500  $\Omega$ )

## 8 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device.

Table 7. Operating conditions (voltage range W)

Symbol	Parameter	Min.	Max.	Unit
V <sub>CC</sub>	Supply voltage	2.5	5.5	V
T <sub>A</sub>	Ambient operating temperature	-40	125	°C

Table 8. AC measurement conditions

Symbol	Parameter	Min.	Max.	Unit
C <sub>bus</sub>	Load capacitance	1(	00	pF
	SCL input rise/fall time, SDA input fall time		50	ns
	Input levels	0.2 V <sub>CC</sub> to 0.8 V <sub>CC</sub>		V
	Input and output timing reference levels	0.3 V <sub>CC</sub> to 0.7 V <sub>CC</sub>		V

Figure 10. AC measurement I/O waveform

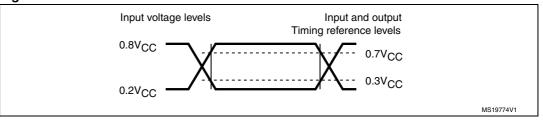


Table 9. Input parameters

Symbol	Parameter <sup>(1)</sup>	Test condition	Min.	Max.	Unit
C <sub>IN</sub>	Input capacitance (SDA)			8	pF
C <sub>IN</sub>	Input capacitance (other pins)			6	pF
$Z_{L}$	Input impedance (E2, E1, E0, WC)(2)	$V_{IN}$ < 0.3 $V_{CC}$	30		kΩ
Z <sub>H</sub>		V <sub>IN</sub> > 0.7 V <sub>CC</sub>	500		kΩ

<sup>1.</sup> Characterized only, not tested in production.

Table 10. Memory cell characteristics

Symbol	Parameter	Test condition	Min.	Max.	Unit
N <sub>cycle</sub>	Endurance	$TA = 25  ^{\circ}C,  2.5  \text{V} < \text{V}_{\text{CC}} < 5.5  \text{V}$	1,000,000	-	Write cycle

Note:

This parameter is not tested but established by characterization and qualification. For endurance estimates in a specific application, please refer to AN2014.

<sup>2.</sup> E2, E1, E0 input impedance when the memory is selected (after a Start condition).

Table 11. DC characteristics (voltage range W, device grade 3)

Symbol	Parameter	Test conditions (see <i>Table 8</i> and <i>Table 10</i> )	Min.	Max.	Unit
I <sub>LI</sub>	Input leakage current (SCL, SDA, E0, E1, E2)	V <sub>IN</sub> = V <sub>SS</sub> or V <sub>CC</sub> device in Standby mode		± 2	μΑ
I <sub>LO</sub>	Output leakage current	SDA in Hi-Z, external voltage applied on SDA: $V_{SS}$ or $V_{CC}$		± 2	μΑ
I <sub>CC</sub>	Supply current (Read)	f <sub>c</sub> = 400 kHz (rise/fall time < 50 ns)		2	mA
I <sub>CC0</sub>	Supply current (Write)	During t <sub>W</sub> , 2.5 V < V <sub>CC</sub> < 5.5 V		5 <sup>(1)</sup>	mA
I <sub>CC1</sub>	Standby supply current	Device not selected <sup>(2)</sup> , V <sub>IN</sub> = V <sub>SS</sub> or V <sub>CC</sub>		5	μΑ
V <sub>IL</sub>	Input low voltage (SCL, SDA, WC)		-0.45	0.3 V <sub>CC</sub>	٧
V <sub>IH</sub>	Input high voltage (SCL, SDA)		0.7 V <sub>CC</sub>	6.5	V
▼IH	Input high voltage (WC, E0, E1, E2)		0.7 V <sub>CC</sub>	V <sub>CC</sub> +0.6	V
V <sub>OL</sub>	Output low voltage	$I_{OL} = 2.1 \text{ mA}, V_{CC} = 2.5 \text{ V} \text{ or}$ $I_{OL} = 3 \text{ mA}, V_{CC} = 5.5 \text{ V}$		0.4	>

<sup>1.</sup> Characterized value, not tested in production.

The device is not selected after power-up, after a Read instruction (after the Stop condition), or after the completion of the internal write cycle tW (tW is triggered by the correct decoding of a Write instruction).

Table 12. 400 kHz AC characteristics

Symbol	Alt.	Parameter <sup>(1)</sup>	Min.	Max.	Unit
f <sub>C</sub>	f <sub>SCL</sub>	Clock frequency	-	400	kHz
t <sub>CHCL</sub>	t <sub>HIGH</sub>	Clock pulse width high	600	-	ns
t <sub>CLCH</sub>	t <sub>LOW</sub>	Clock pulse width low	1300		ns
t <sub>QL1QL2</sub> (2)	t <sub>F</sub>	SDA (out) fall time	20 <sup>(3)</sup>	120	ns
t <sub>XH1XH2</sub>	t <sub>R</sub>	Input signal rise time	(4)	(4)	ns
t <sub>XL1XL2</sub>	t <sub>F</sub>	Input signal fall time	(4)	(4)	ns
t <sub>DXCX</sub>	t <sub>SU:DAT</sub>	Data in set up time	100	-	ns
t <sub>CLDX</sub>	t <sub>HD:DAT</sub>	Data in hold time	0	-	ns
t <sub>CLQX</sub> (5)	t <sub>DH</sub>	Data out hold time	100	-	ns
t <sub>CLQV</sub> <sup>(6)</sup>	t <sub>AA</sub>	Clock low to next data valid (access time)		900	ns
t <sub>CHDL</sub>	t <sub>SU:STA</sub>	Start condition setup time	600	-	ns
t <sub>DLCL</sub>	t <sub>HD:STA</sub>	Start condition hold time	600	-	ns
t <sub>CHDH</sub>	t <sub>SU:STO</sub>	Stop condition set up time	600	-	ns
t <sub>DHDL</sub>	t <sub>BUF</sub>	Time between Stop condition and next Start condition	1300	-	ns
t <sub>W</sub>	t <sub>WR</sub>	Write time	-	5	ms
t <sub>NS</sub> <sup>(2)</sup>		Pulse width ignored (input filter on SCL and SDA) - single glitch	-	80	ns

<sup>1.</sup> Test conditions (in addition to those specified under Operating conditions and AC test measurement conditions in Section 8: DC and AC parameters).

- 2. Characterized only, not tested in production.
- 3. With  $C_L = 10 pF$ .
- 4. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the  $^{12}$ C specification that the input signal rise and fall times be more than 20 ns and less than 300 ns when  $^{1}$ C < 400 kHz.
- 5. The min value for  $t_{CLQX}$  (Data out hold time) of the M24xxx devices offers a safe timing to bridge the undefined region of the falling edge SCL.
- 6.  $t_{CLQV}$  is the time (from the falling edge of SCL) required by the SDA bus line to reach either 0.3  $V_{CC}$  or 0.7  $V_{CC}$ , assuming that  $R_{bus} \times C_{bus}$  time constant is within the values specified in *Figure 11*.

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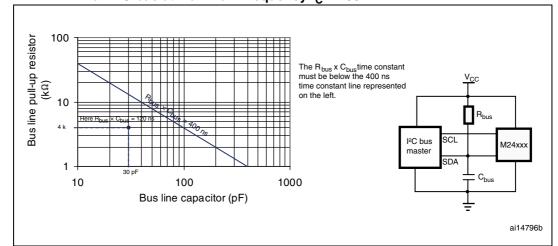
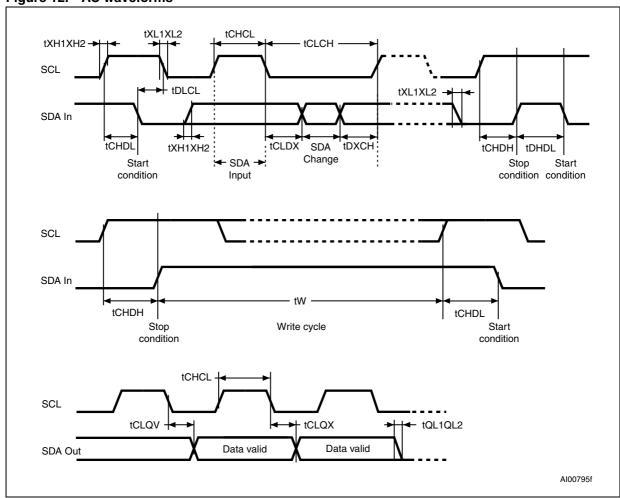


Figure 11. Maximum  $R_{bus}$  value versus bus parasitic capacitance ( $C_{bus}$ ) for an  $I^2C$  bus at maximum frequency  $f_C = 400 \text{ kHz}$ 





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## 9 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

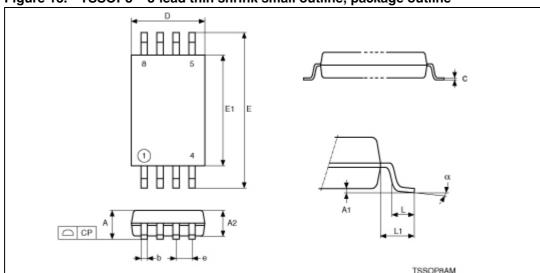


Figure 13. TSSOP8 – 8-lead thin shrink small outline, package outline

Table 13. TSSOP8 – 8-lead thin shrink small outline, package mechanical data

Symbol		millimeters		inches <sup>(1)</sup>		
	Тур.	Min.	Max.	Тур.	Min.	Max.
Α			1.200			0.0472
A1		0.050	0.150		0.0020	0.0059
A2	1.000	0.800	1.050	0.0394	0.0315	0.0413
b		0.190	0.300		0.0075	0.0118
С		0.090	0.200		0.0035	0.0079
СР			0.100			0.0039
D	3.000	2.900	3.100	0.1181	0.1142	0.1220
е	0.650	-	-	0.0256	_	_
E	6.400	6.200	6.600	0.2520	0.2441	0.2598
E1	4.400	4.300	4.500	0.1732	0.1693	0.1772
L	0.600	0.450	0.750	0.0236	0.0177	0.0295
L1	1.000			0.0394		
α		0°	8°		0°	8°

 $<sup>{\</sup>bf 1.} \quad {\bf Values\ in\ inches\ are\ converted\ from\ mm\ and\ rounded\ to\ four\ decimal\ digits.}$ 

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<sup>1.</sup> Drawing is not to scale.

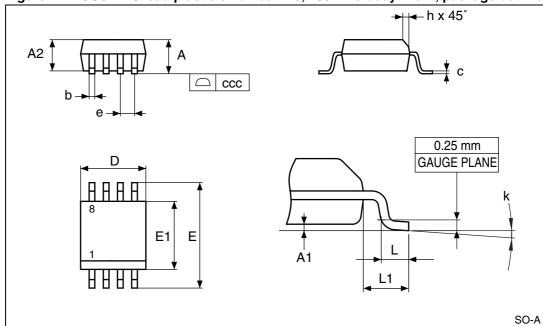


Figure 14. SO8N – 8 lead plastic small outline, 150 mils body width, package outline

1. Drawing is not to scale.

Table 14. SO8N – 8 lead plastic small outline, 150 mils body width, package data

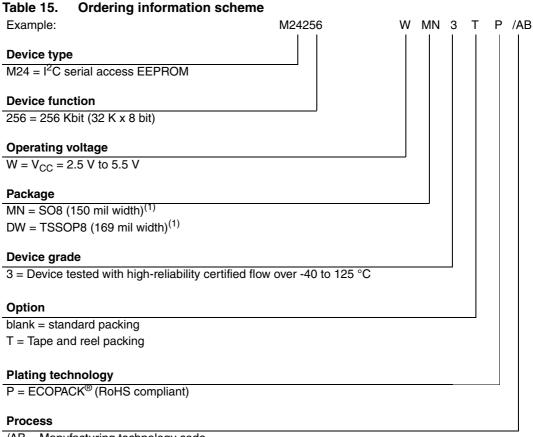
Symbol		millimeters			inches <sup>(1)</sup>	
Syllibol	Тур	Min	Max	Тур	Min	Max
Α			1.750			0.0689
A1		0.100	0.250		0.0039	0.0098
A2		1.250			0.0492	
b		0.280	0.480		0.0110	0.0189
С		0.170	0.230		0.0067	0.0091
ccc			0.100			0.0039
D	4.900	4.800	5.000	0.1929	0.1890	0.1969
E	6.000	5.800	6.200	0.2362	0.2283	0.2441
E1	3.900	3.800	4.000	0.1535	0.1496	0.1575
е	1.270			0.0500		
h		0.250	0.500		0.0098	0.0197
k		0°	8°		0°	8°
L		0.400	1.270		0.0157	0.0500
L1	1.040			0.0409		

1.

5//

Part numbering M24256-125

## 10 Part numbering



/AB = Manufacturing technology code

1. RoHS-compliant and halogen-free (ECOPACK2®)

For a list of available options (speed, package, etc.) or for further information on any aspect of the devices, please contact your nearest ST sales office.

M24256-125 Revision history

# 11 Revision history

Table 16. Document revision history

Date	Revision	Changes
22-Feb-2012	1	Initial release.

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